L Number	Hits	Search Text	DB	Time stamp
-	909	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:15
-	468	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 09:57
-	403	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 09:58
-	1	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and ((releasable released releasing) near1 (layer film material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:08
-	101	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:03
-	63	((((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)) and ((flipchip (flip adj chip)) bump ball)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 11:06
-	179	(mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:10
-	12	((mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:27
-	0	6123895.URPN.	USPAT	2002/09/20 10:16
-	5	("3178807" | "5006417" | "5384087" | "5616421" | "5902943").PN.	USPAT	2002/09/20 10:16
-	1	jp408142106a	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:29
-	156	MIYAJIMA-FUMIO	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:30
-	19	MIYAJIMA-FUMIO	USPAT; EPO	2002/09/20 10:30
-	1	6187243.pn. and (parting adj face)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 14:01
-	1481	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:42
-	39173	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:34

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-	54	(mold near2 (upper lower)) near3 (air adj vent)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 14:59
-	8	((mold near2 (upper lower)) near3 (air adj vent)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 14:59
-	5628	tab near3 lead	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:18
-	1951	(tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:33
-	92	((tab near3 lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated plating electroplated electroplating)) with (electrode terminal pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:34
-	21	((tab near3 lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated plating electroplated electroplating)) with ((electrode terminal pad) near3 (chip die ic)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:29
-	3900	257/787	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
-	1339	257/787 and shape	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
-	57	(257/787 and shape) and leadless	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
-	40537	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:40
-	7365	(mold near2 (upper lower)) and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:37
-	4354	((mold near2 (upper lower)) and (chip die wafer)) and (methor process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:39
-	5701	((mold near2 (upper lower)) and (chip die wafer)) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:39
-	173	(((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:45
-	0	((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and ((releasable released releasing) near (film layer tape))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 11:07
-	12	((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and ((releasable released release releasing) near (film layer tape))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:36
-	0	20020017738.URPN.	USPAT	2003/03/27 12:20

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–	55	((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and (releasable released release releasing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:35
–	43	(((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and (releasable released release releasing)) not (((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and ((releasable released release releasing) near (film layer tape)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 12:24
–	98	5450283.URPN.	USPAT	2003/03/27 14:35
–	759	(((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)	USPAT	2003/03/27 14:35
–	671	((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))	USPAT	2003/03/27 14:35
–	275	(((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and (releasable released release releasing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:36
–	10	(((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and ((releasable released release releasing) near1 (film layer tape))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:43
–	2	6019588.URPN.	USPAT	2003/03/27 14:41
–	16	("4044984" | "4236689" | "4332537" | "4442056" | "4470786" | "4697784" | "4779835" | "5059105" | "5118271" | "5218759" | "5429488" | "5484274" | "5626886" | "5639695" | "5693572" | "5779958").PN.	USPAT	2003/03/27 14:41
–	265	((((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and (releasable released release releasing)) not ((((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip)))) and ((releasable released release releasing) near1 (film layer tape)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:43
–	1	"20030052418"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:32
–	40999	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:41

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-	1694	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:15
-	446	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:45
-	395	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 12:18
-	369	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:17
-	122	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (method process)) and ((die mounting) adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:47
-	53	5474958.URPN.	USPAT	2003/05/08 09:52
-	0	6472252.URPN.	USPAT	2003/05/08 09:59
-	36	("4313718" | "4697784" | "4881884" | "4944908" | "5147821" | "5355283" | "5362679" | "5405255" | "5406699" | "5467253" | "5468999" | "5474958" | "5477611" | "5479051" | "5490324" | "5506756" | "5508565" | "5527743" | "5543658" | "5545922" | "5556807" | "5596227" | "5609889" | "5626886" | "5656549" | "5663106" | "5665281" | "5688716" | "5766649" | "5766650" | "5817545" | "5876765" | "5923959" | "5928595" | "6117382" | "6281588").PN.	USPAT	2003/05/08 09:59
-	3	6117382.URPN.	USPAT	2003/05/08 10:01
-	20	("5034350" | "5114880" | "5147815" | "5222014" | "5239806" | "5313365" | "5331205" | "5366364" | "5458694" | "5488257" | "5578261" | "5597643" | "5598034" | "5608262" | "5609889" | "5614441" | "5615089" | "5646829" | "5755914" | "5830781").PN.	USPAT	2003/05/08 10:02
-	20	("5034350" | "5114880" | "5147815" | "5222014" | "5239806" | "5313365" | "5331205" | "5366364" | "5458694" | "5488257" | "5578261" | "5597643" | "5598034" | "5608262" | "5609889" | "5614441" | "5615089" | "5646829" | "5755914" | "5830781").PN.	USPAT	2003/05/08 10:04
-	7	5923959.URPN.	USPAT	2003/05/08 10:05
-	20	("5355283" | "5362679" | "5406699" | "5467253" | "5468999" | "5474958" | "5477611" | "5479051" | "5490324" | "5506756" | "5508565" | "5527743" | "5543658" | "5545922" | "5556807" | "5596227" | "5609889" | "5656549" | "5663106" | "5688716").PN.	USPAT	2003/05/08 10:10
-	21	5609889.URPN.	USPAT	2003/05/08 10:12
-	0	6428300.URPN.	USPAT	2003/05/08 10:13

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-	29	("3505446" | "3685784" | "3991146" | "4184835" | "4464322" | "4470786" | "4618466" | "4770833" | "4954308" | "5049344" | "5049526" | "5110515" | "5174941" | "5326243" | "5344600" | "5366368" | "5429488" | "5451153" | "5480296" | "5523038" | "5558883" | "5609889" | "5626886" | "5650177" | "5714106" | "5798070" | "5989471" | "6030569" | "6224360").PN.	USPAT	2003/05/08 10:13
-	26	5817545.URPN.	USPAT	2003/05/08 10:18
-	0	6558982.URPN.	USPAT	2003/05/08 10:19
-	6	("5817545" | "5874324" | "5998243" | "6204095" | "6329224" | "6335221").PN.	USPAT	2003/05/08 10:19
-	36	("3930114" | "4043027" | "4437141" | "4455274" | "4460537" | "4470786" | "4688152" | "4778641" | "4823234" | "4859722" | "4861251" | "4868349" | "4890152" | "4893172" | "4935581" | "4954877" | "4954878" | "4961105" | "4972253" | "4975765" | "5019673" | "5049526" | "5093282" | "5108955" | "5132778" | "5136366" | "5153385" | "5191511" | "5216278" | "5218759" | "5241133" | "5296738" | "5328870" | "5355283" | "5370517" | "5395226").PN.	USPAT	2003/05/08 10:23
-	40	5108955.URPN.	USPAT	2003/05/08 10:26
-	7	("4266239" | "4541005" | "4778641" | "4822550" | "4823234" | "4868638" | "4890152").PN.	USPAT	2003/05/08 10:43
-	3	6081978.URPN.	USPAT	2003/05/08 12:10
-	3	("5336272" | "6001671" | "6033933").PN.	USPAT	2003/05/08 12:11
-	113	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (vent vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 12:18
-	389176	"113" not ((((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (method process)) and ((die mounting) adj pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 12:19
-	91	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (vent vacuum)) not ((((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (method process)) and ((die mounting) adj pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 12:19
-	25	5147821.URPN.	USPAT	2003/05/08 12:24
-	2	("4866506" | "4944908").PN.	USPAT	2003/05/08 12:26
-	25	5147821.URPN.	USPAT	2003/05/08 13:43
-	53	5474958.URPN.	USPAT	2003/05/08 13:44
-	4	5776800.URPN.	USPAT	2003/05/08 13:45

-	5	("5101324" | "5130889" | "5309026" | "5394298" | "5474958").PN.	USPAT	2003/05/08 13:45
-	2	5874319.URPN.	USPAT	2003/05/08 13:48
-	21	("3777365" | "3811182" | "4881885" | "4932883" | "5147821" | "5173451" | "5203401" | "5237269" | "5322207" | "5336649" | "5367253" | "5378981" | "5424652" | "5459351" | "5474958" | "5475317" | "5489538" | "5548884" | "5568057" | "5589781" | "5591649").PN.	USPAT	2003/05/08 13:48
-	2	("4866506" | "4944908").PN.	USPAT	2003/05/08 13:53
-	2	("4866506" | "4944908").PN.	USPAT	2003/05/08 13:53
-	5	"6081978"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:17
-	3	("5336272" | "6001671" | "6033933").PN.	USPAT	2003/05/12 08:46
-	740	(memory adj chip) near3 array	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:36
-	471	((memory adj chip) near3 array) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:18
-	137	((memory adj chip) near3 array) and (semiconductor near1 (package device))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:20
-	8	((memory adj chip) near3 array) with known	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:37
-	1406	(memory near chip) near4 array	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:36
-	15	((memory near chip) near4 array) with known	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:37
-	7	(((memory near chip) near4 array) with known) not (((memory adj chip) near3 array) with known)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/12 09:37
-	2102	(tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:33
-	1640	((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:36
-	123	(((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:18
-	94	((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))) and (seal sealed sealing encapsulant encapsulated encapsulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:18

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-	43	((((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))) and (seal sealed sealing encapsulant encapsulated encapsulating).) and (stacked stacking)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:38
-	1916	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:15
-	1562	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:16
-	430	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:17
-	232	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)) and (vias (through adj hole))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:22
-	49	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)) and (vias (through adj hole))) and ((reducing near1 thickness) thinning)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:22
-	129	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)) and (stacked stacking)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:22
-	77	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)) and (stacked stacking)) and (vias (through adj hole))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:22
-	45	((((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)) and (stacked stacking)) and (vias (through adj hole))) not (((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead near1 (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)) and (vias (through adj hole))) and ((reducing near1 thickness) thinning))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:22

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